

深圳市晶泰源电子有限公司

JTY13003

TRANSISTOR(NPN)

FEATURES

Power dissipation

PCM:1.2W(Tamb=25°C)

Collector current

ICM:1.42A

Collector-base voltage

V(BR)CBO: 600V

Operating and storage junction temperature range

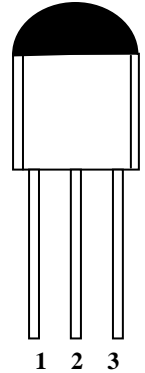
TJ,Tstg:-65°C to -150°C

T0-92

1. BASE

2.COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=1mA, IE=0	600			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	400			V
Emitter-base breakdown voltage	V(BR)EBO	IC=1mA, IC=0	9			V
Collector cut-off current	ICBO	VCB=600V, IE=0			0.5	μA
Collector cut-off current	ICEO	Vce=400V, IB=0			1.0	μA
Emitter cut-off current	IEBO	VEB=9V, IC=0			0.1	μA
DC current gain	HFE	Vce=5V, IC=1mA	10		40	
Collector-emitter saturation voltage	VCE(sat)	IC=0.5A, IB=0.1A			0.5	V
Collector-Base saturation voltage	VBE(sat)	IC=0.5A, IB=0.1A			1.2	V
Storage time	ts	Vcc=5V Ic=0.25A (UI9600)	1.5		5.0	us
Falling Time	tf				1.0	us

深圳市晶泰源电子有限公司

电话：0755-83211536 传真：0755-83206326

深圳市福田区华强北路华强广场C座11C